



FQI11N40TU Information

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Part Number FQI11N40TU

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products

Transistors - FETs, MOSFETs - Single MOSFET N-CH 400V 11.4A I2PAK

DescriptionMOSFET N-CH 400V 11.4A I2PAK**Package**TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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FQI11N40TU Specifications

Manufacturer Part Number FQI11N40TU Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 400V Current - Continuous Drain (Id) @ 25°C 11.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 35nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 147W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 5.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA		
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Package TO-262-3 Long Leads, 12Pak, TO-262AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 400V Current - Continuous Drain (Id) @ 25°C 11.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 35nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 147W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 5.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Manufacturer	Fairchild/ON Semiconductor
Package TO-262-3 Long Leads, I2Pak, TO-262AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 400V Current - Continuous Drain (Id) @ 25°C 11.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 35nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 147W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 5.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case 150 To 262-3 Long Leads, I2Pak, TO-262AA	Category	Discrete Semiconductor Products
Series - M-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 400V Current - Continuous Drain (Id) @ 25°C 11.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 35nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 147W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 5.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case Toology and Capacitan, 12Pak, TO-262AA		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)400VCurrent - Continuous Drain (Id) @ 25°C11.4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.13W (Ta), 147W (Tc)Rds On (Max) @ Id, Vgs480 mOhm @ 5.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Package	TO-262-3 Long Leads, I2Pak, TO-262AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)400VCurrent - Continuous Drain (Id) @ 25°C11.4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.13W (Ta), 147W (Tc)Rds On (Max) @ Id, Vgs480 mOhm @ 5.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Series	-
Drain to Source Voltage (Vdss)400 VCurrent - Continuous Drain (Id) @ 25°C11.4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id5 V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 25 VVgs (Max)±30 VFET Feature-Power Dissipation (Max)3.13W (Ta), 147W (Tc)Rds On (Max) @ Id, Vgs480 mOhm @ 5.7A, 10 VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA 35nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 480 mOhm @ 5.7A, 10V Operating Temperature Supplier Device Package Package / Case 11.4A (Tc) 10V 55°C ≈ 150°C TO Through Hole 12PAK TO-262-3 Long Leads, 12Pak, TO-262AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.13W (Ta), 147W (Tc)Rds On (Max) @ Id, Vgs480 mOhm @ 5.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI2PAKPackage / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	Drain to Source Voltage (Vdss)	400V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As on (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case Sy @ 250μA 35nC @ 10V 1400pF @ 25V 250V 480 mCh 480 mCh 55°C ~ 150°C (TJ) Through Hole Supplier Device Package I2PAK TO-262-3 Long Leads, I2Pak, TO-262AA	Current - Continuous Drain (Id) @ 25°C	11.4A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 480 mOhm @ 5.7A, 10V Operating Temperature Jordan Temperature Mounting Type Through Hole Supplier Device Package TO-262-3 Long Leads, I2Pak, TO-262AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Through Hole Supplier Device Package I2PAK Package / Case 1400pF @ 25V 140	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.13W (Ta), 147W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 5.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	35nC @ 10V
FET Feature - Power Dissipation (Max) 3.13W (Ta), 147W (Tc) Rds On (Max) @ Id, Vgs 480 mOhm @ 5.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Input Capacitance (Ciss) (Max) @ Vds	1400pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 480 mOhm @ 5.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs480 mOhm @ 5.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI2PAKPackage / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	3.13W (Ta), 147W (Tc)
Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	480 mOhm @ 5.7A, 10V
Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	I2PAK
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
		Report errors?

FQI11N40TU Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQI11N40TU Payment Methods



















FQI11N40TU Shipping Methods













If you have any question about FQI11N40TU, please do not hesitate to contact us!

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